		, m	DB	Time stamp
L Number	Hits	Search Text (wafer and (metal adj (film or layer)) and	USPAT:	2003/10/23 10:34
41	241	(attach\$5 or bond\$4) and ((balls adj grid	US-PGPUB;	
		(attach\$5 or bond\$4) and (balls ad) grid	EPO; JPO;	
		adj arrays) or (BGA)) and semiconductor	DERWENT;	İ
į		and (dic\$4 or cut\$4 or separat\$5)) and	IBM TDB	
	ļ	@ad<=20000616	USPAT;	2003/10/23 10:35
42	241	(wafer and (metal adj (film or layer)) and		2003/10/23 10:33
·- 1		(attach\$5 or bond\$4) and ((balls adj grid)	US-PGPUB;	
ì	İ	adi arrays) or ("BGA")) and semiconductor	EPO; JPO;	
		and (dic\$4 or cut\$4 or separat\$5)) and	DERWENT;	
		@ad<=20000616	IBM_TDB	
	,	((wafer same (metal adj (film or layer))	USPAT;	2003/10/23 10:36
43		same (attach\$5 or bond\$4) same ((balls adj	US-PGPUB;	
		grid adj arrays) or ("BGA")) same	EPO; JPO;	
		semiconductor same (dic\$4 or cut\$4 or	DERWENT;	1
		semiconductor same (dicor of cacy) of	IBM TDB	
		separat\$5))) and @ad<=20000616	USPAT	2003/05/20 07:57
-	348	(438/15).CCLS.	USPAT	2002/07/03 08:58
-	258	(438/113).CCLS.		2002/07/03 08:58
-	94	(438/110).CCLS.	USPAT	2002/07/03 08:58
i _	59	(438/114).CCLS.	USPAT	2002/07/03 08:38
_	681	438/15.110.113.114.ccls.	USPAT	2002/12/19 14:38
_	401	439/15 110 113 114 ccls. and test\$3	USPAT	2001/08/07 15:09
-	272	(438/15,110,113,114.ccls. and test\$3) and	USPAT	2001/08/07 15:10
1 ⁻	212	(dice\$4 or cut\$5)		
		(UTCEAR OF CREAD)	USPAT;	2002/02/04 09:53
ŗ -	901	438/15,110,113,114.ccls.	EPO; JPO;	1
			DERWENT	
			USPAT;	2002/02/04 09:54
-	460	438/15,110,113,114.ccls. and test\$3	EPO; JPO;	2002, 02, 01
			DERWENT	0000/00/05 00:26
_	325	(438/15,110,113,114.ccls. and test\$3) and	USPAT;	2002/02/05 08:26
	1	(dic\$5 or cut\$5)	EPO; JPO;	1
		(420)	DERWENT	
	5	(("6077757") or ("6335224") or ("6309943")	USPAT	2003/05/21 08:46
-	,	or ("6309909") or ("6326697")).PN.		1
1	٦		USPAT	2002/02/05 09:49
-	7	or ("6309909") or ("6326697") or		
		or ("6309909") of (632669) / Of		l i
		("5858815") or ("5137836")).PN.	USPAT;	2002/02/05 08:28
-	326	(438/15,110,113,114.ccls. and test\$3) and	EPO; JPO;	
		(dic\$5 or cut\$5)	DERWENT	
				2002/02/05 08:33
_	l o	((438/15,110,113,114.ccls. and test\$3) and	USPAT;	2002/02/03 00:33
		(dic\$5 or cut\$5)) and (magnet\$7 adj	EPO; JPO;	
1		align\$5)	DERWENT	
	170	+ +	USPAT;	2002/02/05 08:32
-	1,0	(dic\$5 or cut\$5)) and (align\$5)	EPO; JPO;	
		(41040 01 04041) /	DERWENT	1
	0705	magnet\$7 adj align\$5	USPAT;	2002/02/05 08:56
-	2705	magnets / adj arrynys	EPO; JPO;	
			DERWENT	1
			USPAT;	2002/02/05 08:37
-	0	(magnet\$7 adj align\$5) and (wafer adj20	EPO; JPO;	
		dielectric adj tape)		
			DERWENT	2002/02/05 09:37
_	0	wafer adj20 dielectric adj tape	USPAT;	2002/02/05 08:37
	1		EPO; JPO;	
1			DERWENT	
	l 0	wafer adj dielectric adj tape	USPAT;	2002/02/05 08:38
-	1	Marci day arotoctio day tape	EPO; JPO;	
1			DERWENT	
		(magnet\$7 adj align\$5) and semiconductor	USPAT;	2002/02/05 08:57
-	248	(magnets / adj alignss) and semiconductor	EPO; JPO;	
1			DERWENT	
Į.	1		USPAT;	2002/02/05 08:49
-	0			2002,02,03
		(charged adj slot)	EPO; JPO;	
1			DERWENT	2002/02/05 09:49
_	0	(magnet\$7 adj align\$5) and (charged adj	USPAT;	2002/02/05 08:49
	1	slot)	EPO; JPO;	
			DERWENT	
1	613	(magnet\$7 adj align\$5) and ring	USPAT;	2002/02/05 08:50
1-	1 613	/magnost, as a sample of the same of the s	EPO; JPO;	}
			DERWENT	
1	l		<u> </u>	

				2002/02/05 08:51
_	47	((magnet\$7 adj align\$5) and ring) and semiconductor	USPAT; EPO; JPO;	2002/02/03 08:31
			DERWENT	2002/02/05 08:56
	3066	optically adj align\$5	USPAT; EPO; JPO;	2002/02/03 00:30
			DERWENT	
	610	(optically adj align\$5) and semiconductor	USPAT;	2002/02/05 08:57
-	612	(optically adj allymps) and semiconducted	EPO; JPO;	
			DERWENT	
_	8	(("6077757") or ("6335224") or ("6309943")	USPAT	2003/06/02 08:10
		or ("6309909") or ("6326697") or		
		("5858815") or ("5137836") or		
		("4781969")).PN.	USPAT;	2002/07/03 08:13
-	10260	wood.inv.	US-PGPUB;	2002/0//03 00:10
			EPO; JPO;	
		i	DERWENT;	1
			IBM_TDB	
_	539	wood.inv. and alan	USPAT;	2002/07/03 08:13
			US-PGPUB;	
			EPO; JPO;	1
			DERWENT; IBM TDB	
		, , , and alan) and (migron add	USPAT;	2002/07/03 08:14
-	232	(wood.inv. and alan) and (micron adj	US-PGPUB;	2502,51,55
		technology)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	1	("6268650").PN.	USPAT	2002/12/20 10:24
_	425	(438/15).CCLS.	USPAT	2002/07/08 08:43 2002/07/08 08:57
-	331		USPAT	2002/07/08 08:57
-	140		USPAT	2002/07/08 08:57
-	90		USPAT	2002/07/08 08:43
-	425 331	1	USPAT	2002/07/08 08:57
]	140		USPAT	2002/07/08 08:57
_ ′	90	(438/114).CCLS.	USPAT	2002/07/08 14:32
_	13	(("6389689") or ("5977629") or ("5796170")	USPAT	2002/07/08 10:35
		or ("6326700") or ("6268650") or		
		("5858815") or ("5817535") or ("5770032")		
		or ("4781969") or ("5073840") or ("5696033") or ("5834839") or		
		("6160714")).PN.		
	8	1	USPAT	2002/07/09 09:56
_	Ĭ	or ("6077757") or ("6326697") or		
		("6165885") or ("5834320") or		
	ļ	("4781969")).PN.	HCDAM.	2002/12/19 15:00
-	0	(wafer adj (bond\$3 or attach\$3) near4	USPAT; US-PGPUB;	2002/12/19 13:00
		(dielectric adj (layer or film))) same test\$3 same (cut\$4 or dic\$3 or separat\$3)	EPO; JPO;	
		restablished (cutta of dicta of sebarata)	DERWENT;	
			IBM_TDB	
_	0	(wafer adj (bond\$3 or attach\$3) near4	USPAT;	2002/12/19 14:07
1		(dielectric adi (layer or film))) same	US-PGPUB;	
		test\$3 same (cut\$4 or dic\$3 or separat\$3)	EPO; JPO;	
			DERWENT; IBM TDB	
1		wafer adj (bond\$3 or attach\$3) near4	USPAT;	2002/12/19 14:07
-	19	(dielectric adj (layer or film))	US-PGPUB;	
		(dietectite ad) (tayor of titm)/	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/10/10 14 00
-	0	(wafer adj (bond\$3 or attach\$3) near4	USPAT;	2002/12/19 14:38
		(dielectric adj (layer or film))) same	US-PGPUB; EPO; JPO;	
		test\$3	DERWENT;	
1			IBM TDB	
_	963	438/15,110,113,114.ccls.	USPĀT	2002/12/19 14:38
1 -	1 . 503	1300,10,110,110,111.0010.		

				2002/12/19 14:38
-	1212	438/15,110,113,114.ccls.	USPAT; US-PGPUB;	2002/12/19 14:38
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	0	438/15,110,113,114.ccls. and ((wafer adj	USPAT;	2002/12/19 14:40
-	١	(bond\$3 or attach\$3) near4 (dielectric adj	US-PGPUB;	
		(layer or film))) same test\$3)	EPO; JPO;	
		(layer of film, // bame total,	DERWENT;	
			IBM_TDB	
-	9	(wafer adj (dielectric adj (layer or	USPAT;	2002/12/20 08:18
		film))) same test\$3	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		/#C1/C071/4#\	IBM_TDB USPAT	2002/12/19 15:19
-	13	(("5834839") or ("6389689") or ("6160714")	USPAI	2002/12/19 13:19
Ì		or ("5977629") or ("6326700") or		
		("6268650") or ("5858815") or ("5817535")		
1		or ("5770032") or ("5796170") or ("4781969") or ("5073840") or		
1		("4781989") OI (3073840) OI ("5696033")).PN.		
	0.5	wafer same dielectric same test\$3 same	USPAT;	2002/12/20 08:42
-	83	(cut\$3 or dic\$3 or slic\$3)	US-PGPUB;	
		1 (6000) 01 01070 01 0110707	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	78		USPAT;	2002/12/20 09:38
		(cut\$3 or dic\$3 or slic\$3)) and	US-PGPUB;	
		semiconductor	EPO; JPO;	İ
			DERWENT;	
			IBM_TDB USPAT;	2002/12/20 09:35
-	348	(wafer same (dielectric adj (layer or	US-PGPUB;	2002/12/20 03:33
		film))) same test\$3	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	322	((wafer same (dielectric adj (layer or	USPĀT;	2002/12/20 09:38
-	322	film))) same test\$3) and semiconductor	US-PGPUB;	[
			EPO; JPO;	İ
			DERWENT;	
1			IBM_TDB	0000/10/00 00:30
-	98	(((wafer same (dielectric adj (layer or	USPAT; US-PGPUB;	2002/12/20 09:39
ĺ	1	film))) same test\$3) and semiconductor)	EPO; JPO;	
		and (cut\$3 or dic\$3)	DERWENT;	
1	1		IBM TDB	
		/#6424022"\ PN	USPAT	2002/12/20 10:24
-	$\frac{1}{3}$	("6424023").PN. (("5897337") or ("5858815") or	USPAT	2002/12/23 11:53
1-	3	("6389689")).PN.		
1_	2	(("5897337") or ("6389689")).PN.	USPAT	2002/12/23 11:53
_	9187	1	USPAT;	2003/05/20 07:59
	1	semiconductor	US-PGPUB;]
1			EPO; JPO;	
1			DERWENT;]
		100000	IBM_TDB USPAT;	2003/05/20 08:02
-	4418	(((balls adj grid adj arrays) or (BGA))	USPAT; US-PGPUB;	2003/03/20 00.02
		and semiconductor) and (dic\$4 or cut\$4 or	EPO; JPO;	
		separat\$5)	DERWENT;	
			IBM TDB	
	4476	(((balls adj grid adj arrays) or (BGA))	USPAT;	2003/05/20 08:04
-	44/6	and semiconductor) and (dic\$4 or cut\$4 or	US-PGPUB;	
		separat\$5 or saw\$4)	EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
_	955	((((balls adj grid adj arrays) or (BGA))	USPAT;	2003/05/20 08:04
		and semiconductor) and (dic\$4 or cut\$4 or	US-PGPUB;	
		separat\$5)) and (metal adj (film or	EPO; JPO;	
	1	layer))	DERWENT; IBM TDB	
			TDM TOD	1

		(201)	USPAT;	2003/05/20 08:04
-	970	((((balls adj grid adj arrays) or (BGA))	USPAT; US-PGPUB;	2003/03/20 00:04
	1	and semiconductor) and (dic\$4 or cut\$4 or separat\$5 or saw\$4)) and (metal adj (film	EPO; JPO;	
	1	or layer))	DERWENT;	
ŀ		or layer,,	IBM TDB	
	1	("20010052642").PN.	US-PGPUB	2003/05/20 08:12
1 _	472	wafer and (metal adj (film or layer)) and	USPAT;	2003/05/20 08:52
-	1 7/2	(attach\$5 or bond\$4) and ((balls adj grid	US-PGPUB;	İ
1	1	adi arrays) or (BGA)) and semiconductor	EPO; JPO;	
	1	and (dic\$4 or cut\$4 or separat\$5)	DERWENT;	į
			IBM_TDB	2003/10/23 10:34
-	233	(wafer and (metal adj (film or layer)) and	USPAT; US-PGPUB;	2003/10/23 10.54
	1	(attach\$5 or bond\$4) and ((balls adj grid	EPO; JPO;	
1		adj arrays) or (BGA)) and semiconductor and (dic\$4 or cut\$4 or separat\$5)) and	DERWENT;	
	!	@ad<=20000616	IBM TDB	
	212		USPAT;	2003/05/21 08:23
-	212	and (attach\$5 or bond\$4) and ((balls adj	US-PGPUB;	
		grid adj arrays) or (BGA)) and	EPO; JPO;	
		semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
i		separat\$5)) and @ad<=20000616) and (dic\$5	IBM_TDB	
		or cut\$6 or saw\$5)		2003/05/20 09:06
-	206	((wafer and (metal adj (film or layer))	USPAT; US-PGPUB;	2003/03/20 09:00
		and (attach\$5 or bond\$4) and ((balls adj	EPO; JPO;	
1		grid adj arrays) or (BGA)) and semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
}		semiconductor and (dic34 of cut)4 of separat\$5)) and @ad<=20000616) and (dic\$5	IBM TDB	
	İ	or cut\$6)		
	1	(((wafer adj semiconductor) same (metal	USPAT;	2003/05/20 10:06
-	1	adi (film or layer)) same (attach\$5 or	US-PGPUB;	
		bond\$4) same ((balls adj grid adj arrays)	EPO; JPO;	
	j	or (BGA)) same (dic\$4 or cut\$4 or	DERWENT;	
	1	separat\$5)) same (dic\$5 or cut\$6 or	IBM_TDB	
		saw\$5)) and @ad<=20000616	HCDAM.	2003/05/21 09:00
_	212	((wafer and (metal adj (film or layer))	USPAT; US-PGPUB;	2003/03/21 03:00
		and (attach\$5 or bond\$4) and ((balls adj	EPO; JPO;	
	ļ	grid adj arrays) or (BGA)) and semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
1		separat\$5)) and @ad<=20000616) and (dic\$5	IBM TDB	
	Ĭ	or cut\$6 or saw\$5)	_	
i_	172	(((wafer and (metal adj (film or layer))	USPAT;	2003/05/21 09:24
-	1	and (attach\$5 or bond\$4) and ((balls ad)	US-PGPUB;	
		grid adj arrays) or (BGA)) and	EPO; JPO;	
		semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616) and (dic\$5	IBM_TDB	
		or cut\$6 or saw\$5)) and dic\$5 (((wafer and (metal adj (film or layer))	USPAT;	2003/05/21 09:35
-	92	and (attach\$5 or bond\$4) and ((balls adj	US-PGPUB;	
		grid adj arrays) or (BGA)) and	EPO; JPO;	
	1	semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616) and (dic\$5	IBM_TDB	
		or cuts6 or saw\$5)) and (dicing or diced)		2002/05/21 00:26
_	70	((((wafer and (metal adj (film or layer))	USPAT;	2003/05/21 09:36
		and (attach\$5 or bond\$4) and ((balls adj	US-PGPUB; EPO; JPO;	
	1	grid adj arrays) or (BGA)) and	DERWENT;	
		semiconductor and (dic\$4 or cut\$4 or separat\$5)) and @ad<=20000616) and (dic\$5	IBM TDB	
		or cut\$6 or saw\$5)) and (dicing or	1	
		diced)) and (individual\$3 or each)		
_	70	((((wafer and (metal adj (film or layer))	USPAT;	2003/05/21 09:36
1	'0	and (attach\$5 or bond\$4) and ((balls ad)	US-PGPUB;	
		grid adj arrays) or (BGA)) and	EPO; JPO;	
		semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616) and (dic\$5	IBM_TDB	
	1	or cut\$6 or saw\$5)) and (dicing or		
1		diced)) and (individual\$3)		<u></u>

-	and (attach\$5 or bond\$4) and ((balls adj grid adj arrays) or (BGA)) and semiconductor and (dic\$4 or cut\$4 or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 09:37
_	diced)) and (individual\$3 adj device)	USPAT	2003/06/02 09:37